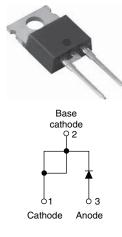
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



TO-220AC

PRODUCT SUMMARY								
Package	TO-220AC							
I _{F(AV)}	8 A							
V _R	600 V							
V _F at I _F	1.7 V							
t _{rr} (typ.)	18 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- \bullet Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08TB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current	۱ _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		60	А					
Maximum repetitive forward current	I _{FRM}		24						
Maximum neuror discinction	Б	T _C = 25 °C	36	W					
Maximum power dissipation	P _D	T _C = 100 °C	14	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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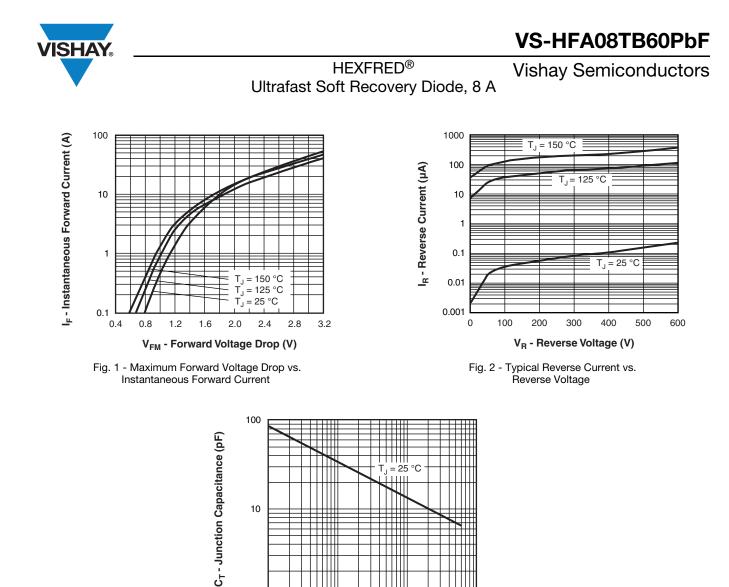
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
		I _F = 8.0 A		-	1.4	1.7	V		
Maximum forward voltage	V _{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1			
		I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse	I _{RM}	$V_{R} = V_{R}$ rated	See fig. 2	-	0.3	5.0	μA		
leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	100	500			
Junction capacitance	CT	V _R = 200 V See fig. 3		-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$) A/µs, V _R = 30 V	-	18	-	ns		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	37	55			
	t _{rr2}	T _J = 125 °C		-	55	90			
Deals receiver a surrent	I _{RRM1}	T _J = 25 °C		-	3.5	5.0	A nC		
Peak recovery current	I _{RRM2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	4.5	8.0			
	Q _{rr1}	T _J = 25 °C		-	65	138			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	124	360			
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A /		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	MIN.	TYP.	MAX.	UNITS						
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	3.5					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Woight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC		HFA0	8TB60					

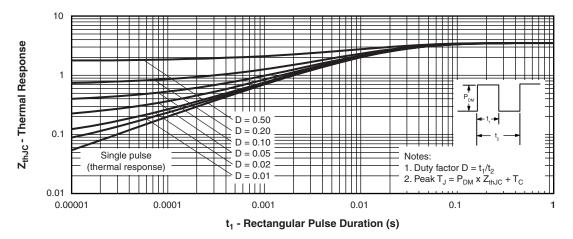
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100

1000



10

V_R - Reverse Voltage (V) Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

1

1



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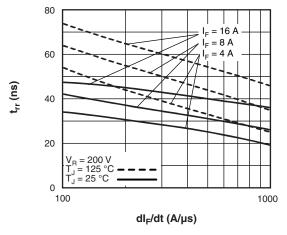
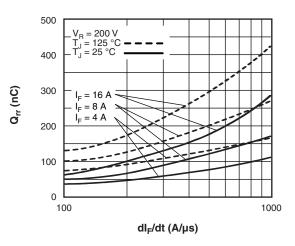


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt



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Fig. 7 - Typical Stored Charge vs. dl_F/dt

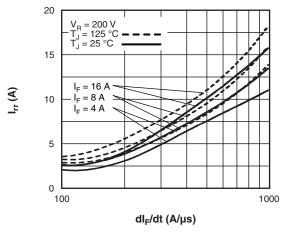


Fig. 6 - Typical Recovery Current vs. dI_F/dt

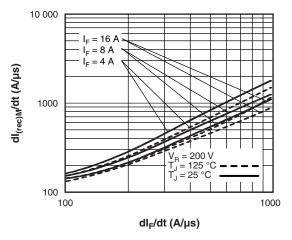


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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HEXFRED® Ultrafast Soft Recovery Diode, 8 A

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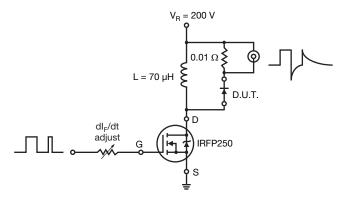


Fig. 9 - - Reverse Recovery Parameter Test Circuit

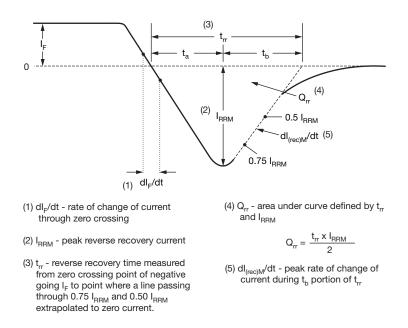
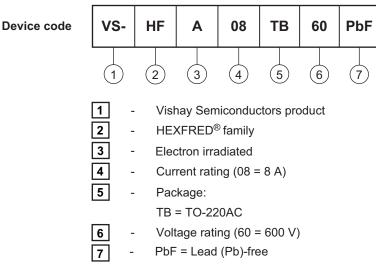


Fig. 10 - Reverse Recovery Waveform and Definitions

- **Vishay Semiconductors**
- HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



ORDERING INFORMATION TABLE



Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95221							
Part marking information	www.vishay.com/doc?95224							

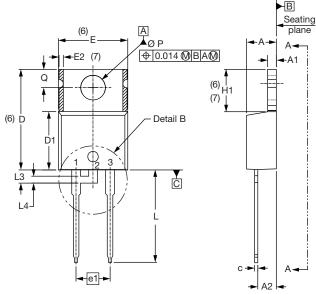


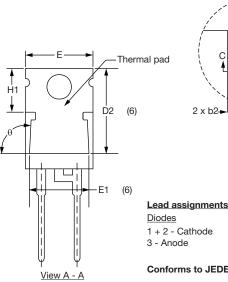
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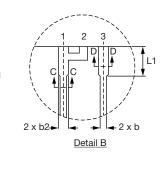
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040		e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4	H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068		L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4	L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024		L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4	L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3	ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355		Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6	θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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